

### Quad $\overline{S}$ - $\overline{R}$ Latch

The TC74HC279A is a high speed CMOS QUAD S-R LATCH fabricated with silicon gate C<sup>2</sup>MOS technology.

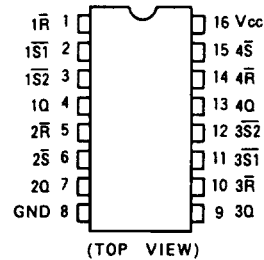
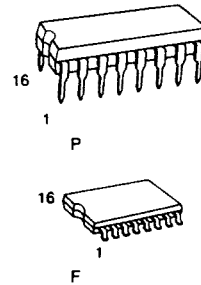
It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

Each latch has an independent Q output and Set and Reset inputs.  $\overline{S}$  and  $\overline{R}$  are active low. When  $\overline{S}$  input is low, the Q output goes high and when  $\overline{R}$  input is low, the Q output goes low. When both  $\overline{S}$  and  $\overline{R}$  are low,  $\overline{S}$  takes precedence resulting Q = low. When both of  $\overline{S}$  and  $\overline{R}$  are held high, Q output doesn't change.

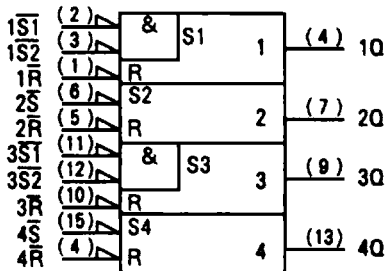
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

### Features

- High Speed:  $t_{pd} = 12\text{ns(Typ.)}$  at  $V_{CC} = 5\text{V}$
- Low Power Dissipation:  $I_{CC} = 2\mu\text{A(Max.)}$  at  $T_a = 25^\circ\text{C}$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC(\text{Min.})}$
- Output Drive Capability: 10 LSTTL Loads
- Symmetrical Output Impedance:  $I_{OH} = I_{OL} = 4\text{mA(Min.)}$
- Balanced Propagation Delays:  $t_{pLH} = t_{pHL}$
- Wide Operating Voltage Range:  $V_{CC(\text{opr})} = 2\text{V} \sim 6\text{V}$
- Pin and Function Compatible with 74LS279



Pin Assignment



IEC Logic Symbol

Truth Table

Inputs		Outputs
$\overline{S\#}$	R	Q
H	H	$Q_n$
L	H	H
H	L	L
L	L	H

Note:

$Q_n$  - The level of Q before the indicated input condition were established

# - For latches with double  $\overline{S}$  input.

H = Both  $\overline{S}$  input high

L = One of both inputs low

## Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply Voltage Range	$V_{CC}$	-0.5 - 7	V
DC Input Voltage	$V_{IN}$	-0.5 - $V_{CC} + 0.5$	V
DC Output Voltage	$V_{OUT}$	-0.5 - $V_{CC} + 0.5$	V
Input Diode Current	$I_{IK}$	±20	mA
Output Diode Current	$I_{OK}$	±20	mA
DC Output Current	$I_{OUT}$	±25	mA
DC $V_{CC}$ /Ground Current	$I_{CC}$	±50	mA
Power Dissipation	$P_D$	500(DIP)*180(SOIC)	mW
Storage Temperature	$T_{stg}$	-65 - 150	°C
Lead Temperature 10sec	$T_L$	300	°C

\*500mW in the range of  $T_a = -40^\circ\text{C} \sim 65^\circ\text{C}$ . From  $T_a = 65^\circ\text{C}$  to  $85^\circ\text{C}$  a derating factor of -10mW/°C shall be applied until 300mW.

## Recommended Operating Conditions

Parameter	Symbol	Value	Unit
Supply Voltage	$V_{CC}$	2 - 6	V
Input Voltage	$V_{IN}$	0 - $V_{CC}$	V
Output Voltage	$V_{OUT}$	0 - $V_{CC}$	V
Operating Temperature	$T_{opr}$	-40 - 85	°C
Input Rise and Fall Time	$t_r, t_f$	0 - 1000( $V_{CC} = 2.0\text{V}$ ) 0 - 500( $V_{CC} = 4.5\text{V}$ ) 0 - 400( $V_{CC} = 6.0\text{V}$ )	ns

## DC Electrical Characteristics

Parameter	Symbol	Test Condition	$T_a = 25^\circ\text{C}$			$T_a = -40 \sim 85^\circ\text{C}$		Unit		
			$V_{CC}$	Min.	Typ.	Max.	Min.		Max.	
High-Level Input Voltage	$V_{IH}$	-	2.0	1.5	-	-	1.5	-	V	
			4.5	3.15	-	-	3.15	-		
			6.0	4.2	-	-	4.2	-		
Low-Level Input Voltage	$V_{IL}$	-	2.0	-	-	0.5	-	0.5	V	
			4.5	-	-	1.35	-	1.35		
			6.0	-	-	1.8	-	1.8		
High-Level Output Voltage	$V_{OH}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -20\mu\text{A}$	2.0	1.9	2.0	-	1.9	-	V
				4.5	4.4	4.5	-	4.4	-	
			$I_{OH} = -4\text{mA}$ $I_{OH} = -5.2\text{mA}$	4.5	4.18	4.31	-	4.13	-	
				6.0	5.68	5.80	-	5.63	-	
Low-Level Output Voltage	$V_{OL}$	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 20\mu\text{A}$	2.0	-	0.0	0.1	-	0.1	V
				4.5	-	0.0	0.1	-	0.1	
			$I_{OL} = 4\text{mA}$ $I_{OL} = 5.2\text{mA}$	4.5	-	0.17	0.26	-	0.33	
				6.0	-	0.18	0.26	-	0.33	
Input Leakage Current	$I_{IN}$	$V_{IN} = V_{CC}$ or GND	6.0	-	-	±0.1	-	±1.0	$\mu\text{A}$	
Quiescent Supply Current	$I_{CC}$	$V_{IN} = V_{CC}$ or GND	6.0	-	-	2.0	-	20.0		

**AC Electrical Characteristics (C<sub>L</sub> = 15pF, V<sub>CC</sub> = 5V, Ta = 25°C)**

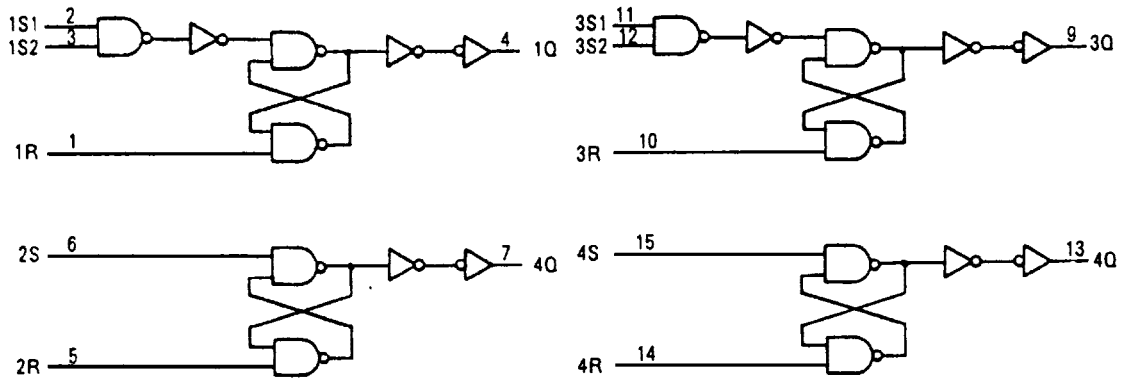
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Output Transition Time	t <sub>TLH</sub> t <sub>THL</sub>	–	–	4	8	ns
Propagation Delay Time (ST, S2-Q)	t <sub>pLH</sub> t <sub>pHL</sub>	–	–	12	22	
Propagation Delay Time (S-Q)	t <sub>pLH</sub> t <sub>pHL</sub>	–	–	9	17	
Propagation Delay Time (R-Q)	t <sub>pLH</sub> t <sub>pHL</sub>	–	–	11	20	

**AC Electrical Characteristics (C<sub>L</sub> = 50pF, Input t<sub>r</sub> = t<sub>f</sub> = 6ns)**

Parameter	Symbol	Test Condition	Ta = 25°C				Ta = -40 ~ 85°C		Unit
			V <sub>CC</sub>	Min	Typ.	Max.	Min.	Max.	
Output Transition Time	t <sub>TLH</sub> t <sub>THL</sub>	–	2.0	–	30	75	–	95	ns
			4.5	–	8	15	–	19	
			6.0	–	7	13	–	16	
Propagation Delay Time (ST, S2-Q)	t <sub>pLH</sub> t <sub>pHL</sub>	–	2.0	–	45	130	–	165	
			4.5	–	15	26	–	33	
			6.0	–	13	22	–	28	
Propagation Delay Time (S-Q)	t <sub>pLH</sub> t <sub>pHL</sub>	–	2.0	–	38	100	–	125	
			4.5	–	12	20	–	25	
			6.0	–	10	17	–	21	
Propagation Delay Time (R, Q)	t <sub>MAX</sub>	–	2.0	–	42	120	–	150	MHz
			4.5	–	14	24	–	30	
			6.0	–	12	20	–	26	
Input Capacitance	C <sub>IN</sub>	–	–	5	10	–	10	pF	
Power Dissipation Capacitance	C <sub>PD(1)</sub>	–	–	18	–	–	–		

Note (1) C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:

$$I_{CC(OPN)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2(\text{per Decoder})$$



Logic Diagram